

ABSTRAC OF THE DISCLOSURE

A method of forming a conductive pattern such as an electrode on a compound semiconductor layer includes the steps of forming a first organic layer on the compound semiconductor layer, forming a second layer on the first organic layer, the
5 second layer being resistant to plasma ashing, forming a pattern including a first aperture in the second layer, forming a second aperture in the first organic layer by the plasma ashing of the first organic layer using a mask of the pattern
10 including the first aperture to expose the compound semiconductor layer in the second aperture, depositing a conductive layer over a region including the compound semiconductor layer exposed in the second aperture and the second layer, and forming the conductive pattern on the
15 compound semiconductor layer by a lift-off process.